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TRANSMITTAL FORM

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Application Number	10/006,704	
Filing Date	December 10, 2001	
First Named Inventor	Shane J. Trapp	
Group Art Unit	1765	
Examiner Name	Lynette Umez Eronini	
Attorney Docket Number	M4065.0369/P369-A	

ENCLOSURES (check all that apply)				
Fee Transn	nittal Form	Assignment Papers (for an Application)	After Allowance Communication to Group	
Fee A	Attached	Drawing(s)	Appeal Communication to Board of Appeals and Interferences	
X Amendmen	t/Reply	Licensing-related Papers	Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)	
After	Final	Petition	Proprietary Information	
Affida	vits/declaration(s)	Petition to Convert to a Provisional Application	Status Letter	
Extension of	of Time Request	Power of Attorney, Revocation Change of Correspondence Address	Other Enclosure(s) (please identify below)	
Express Ab	andonment Request	Terminal Disclaimer	Amendment Transmittal	
Information Disclosure Statement		Request for Refund		
Certified Co	ppy of Priority s)	CD, Number of CD(s)		
Response to Incomplete	o Missing Parts/ Application	Remarks		
Respo	onse to Missing Parts 37 CFR 1.52 or 1.53			
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT				
Firm or Individual Name	DICKSTEIN SHAPIRO MORIN & OSHINSKY LLP Thomas J. D'Amio			
Signature	Jan San San San San San San San San San S			
Date	April 25, 2003			



Docket No.: M4065.0369/P369-A (PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of: Shane J. Trapp

Application No.: 10/006,704

Filed: December 10, 2001

For: METHOD AND COMPOSITION FOR PLASMA ETCHING OF A SELF-ALIGNED

CONTACT OPENING

Group Art Unit: 176

AMENDMENT

BOX: Non-Fee Amendment Commissioner for Patents Washington, DC 20231

Dear Sir:

This paper is in response to the Office Action dated January 29, 2003, rejecting claims 26-35. Please amend the above-captioned U.S. Patent application as follows.

IN THE CLAIMS:

Please rewrite claims 26, 27, 32, 33 and 35 as follows:

26. (amended) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition comprising:

a gaseous mixture consisting essentially of at least one fluorocarbon and ammonia.